

REASUNOS

RS20N60D

N Channel MOSFET

 Lead Free Package and Finish

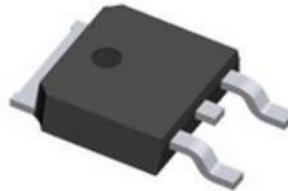
Applications:

- PWM applications
- Load switch
- Power management

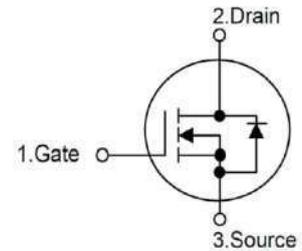
I_D	$R_{DS(ON)}(Max.)$	V_{DSS}
60A	6.5mΩ	20V

Features:

- $V_{DS}=20V$; $I_D=60A$
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 4.5V$
 $R_{ds(on)} < 10m\Omega @ V_{GS} = 2.5V$
- Ultra Low On-Resistance
- High UIS and UIS 100% Test
- RoHS Compliant



TO-252(DPAK) top view



Ordering Information

Part Number	Package	Marking
RS20N60D	TO-252	RS20N60D

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise specified

Symbol	Parameter	RS20N60D	Units
V_{DSS}	Drain-to-Source Voltage	20	V
I_D	Continuous Drain Current ($T_c=25^\circ C$)	60	A
	Continuous Drain Current $T_c=100^\circ C$	39	
I_{DM}	Pulsed Drain Current (Note*1)	240	
PD	Power Dissipation ($T_c=25^\circ C$)	37	W
VGS	Gate-to-Source Voltage	± 20	V
EAS	Single Pulse Avalanche Energy (Note*2)	47.6	mJ
TL TPKG	Maximum Temperature for Soldering	300 260	$^\circ C$
	Leads at 0.063in(1.6mm)from Case for 10 seconds		
	Package Body for 10 seconds		
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 175	

*Drain Current Limited by Maximum Junction Temperature

Caution:Stresses greater than those listed in the“Absolute Maximum Ratings”Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS20N60D	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	4	$^\circ C/W$	Drain lead soldered to water cooled heatsink,PD adjusted for a peak junction temperature of $+175^\circ C$.

REASUNOS

RS20N60D

OFF Characteristics $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain-to-source Breakdown Voltage	20	--	--	V	$V_{GS}=0V, I_D=250\mu A$
IDSS	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=20V, V_{GS}=0V$
IGSS	Gate-to-Source Forward Leakage	--	--	100	nA	$V_{GS}=+12V, V_{DS}=0V$
	Gate-to-Source Reverse Leakage	--	--	-100		$V_{GS}=-12V, V_{DS}=0V$

ON Characteristics $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain-to-Source On-Resistance (Note*3)	--	4.8	6.5	m Ω	$V_{GS}=4.5V, I_D=25A$
		--	6.8	10.0	m Ω	$V_{GS}=2.5V, I_D=15A$
VGS(TH)	Gate Threshold Voltage	0.4	0.7	1.0	V	$V_{GS}=V_{DS}, I_D=250\mu A$

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn-on Delay Time	--	15	--	nS	$V_{DS}=10V$ $V_{GS}=4.5V$ $I_D=25A$ $R_G=3\Omega$
trise	Rise Time	--	37	--		
td(OFF)	Turn-OFF Delay Time	--	52	--		
tfall	Fall Time	--	21	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	1799	--	pF	$V_{GS}=0V$ $V_{DS}=10V$ $f=1.0MHz$
Coss	Output Capacitance	--	298	--		
Crss	Reverse Transfer Capacitance	--	283	--		
Qg	Total Gate Charge	--	23	--	nC	$V_{DS}=10V$ $I_D=25A$ $V_{GS}=4.5V$
Qgs	Gate-to-Source Charge	--	5	--		
Qgd	Gate-to-Drain("Miller") Charge	--	7	--		

Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
ISD	Source-Drain Current(Body Diode)	--	--	60	A	
ISDM	Pulsed Source-Drain Current(Body Diode)	--	--	240	A	Maximum Pulsed Drain to Source Diode Forward Current
VSD	Diode Forward Voltage	--	--	1.3	V	IS=30A,VGS=0V
trr	Reverse Recovery Time	--	25	--	nS	VGS=0V
Qrr	Reverse Recovery Charge	--	21	--	nC	IF=25A,di/dt=100A/μs

Notes:

- *1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- *2. EAS condition: TJ=25°C, VDD=10V, VG=4.5V, L=0.5mH, RG=25Ω, IAS=13.8A
- *3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Feature curve

Figure 1. Output Characteristics (TJ = 25°C)

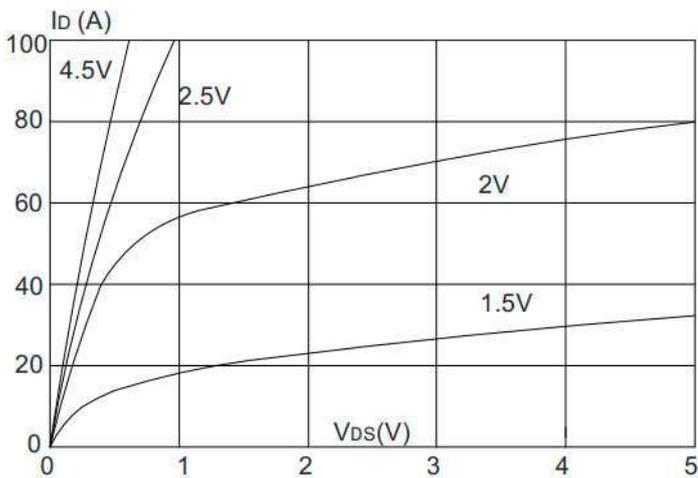


Figure 2. Transfer Characteristics

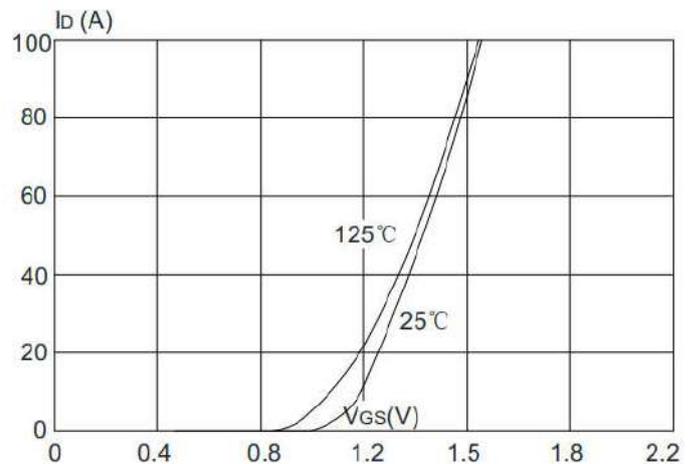


Figure 3. On-Resistance vs. Drain Current

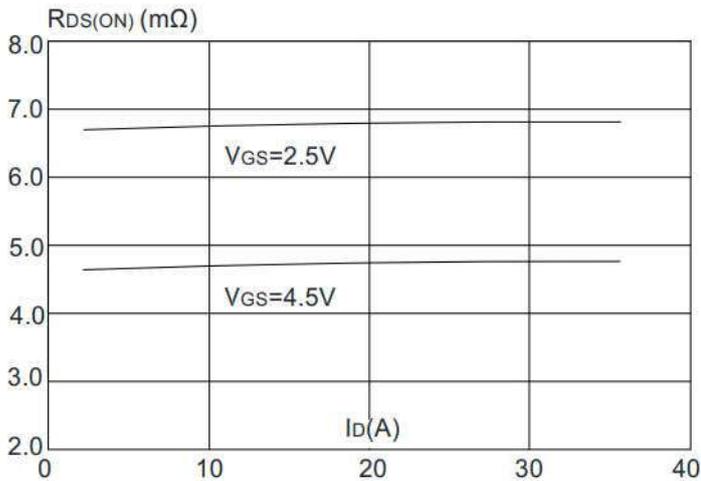


Figure 4: Body Diode Characteristics

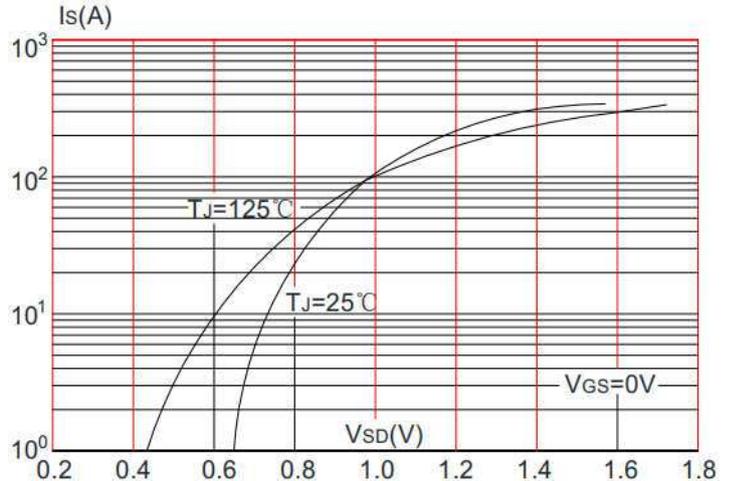


Figure 5. Gate Charge Characteristics

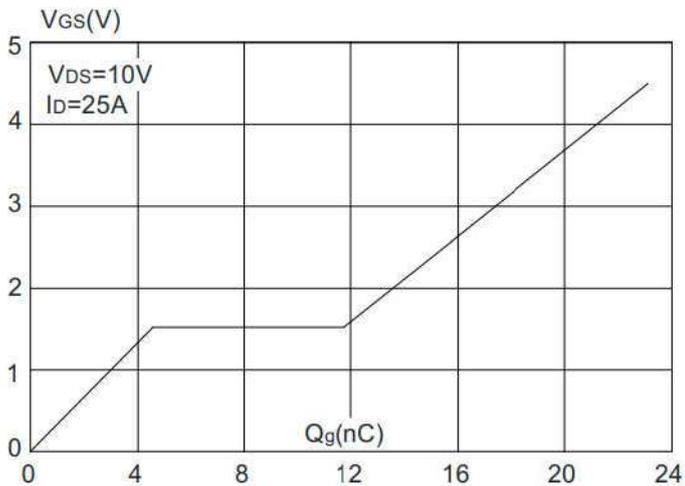


Figure 6. Capacitance Characteristics

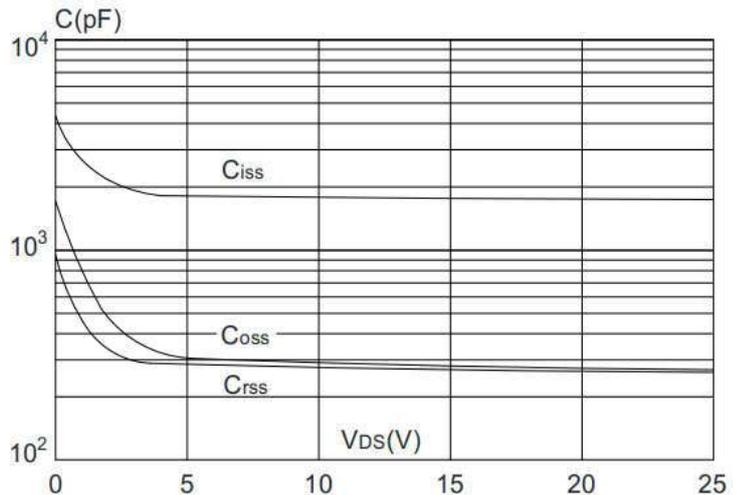


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

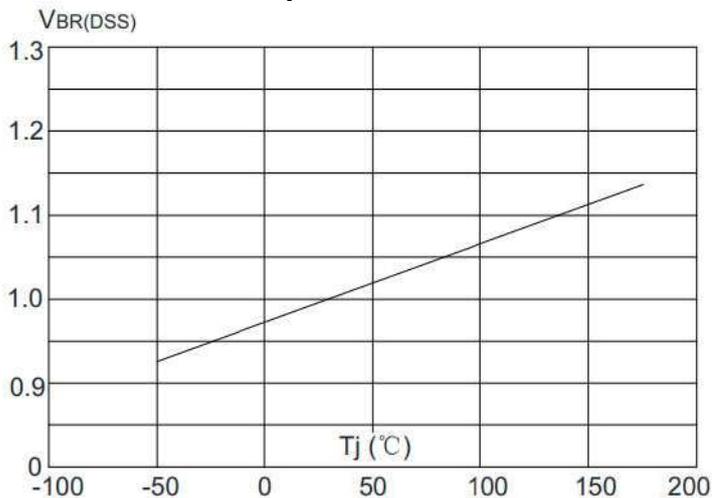


Figure 8: Normalized on Resistance vs. Junction Temperature

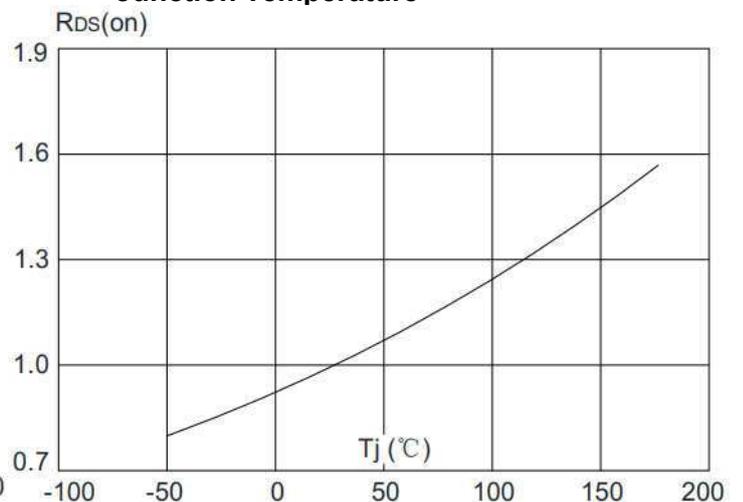


Figure 9: Maximum Safe Operating Area

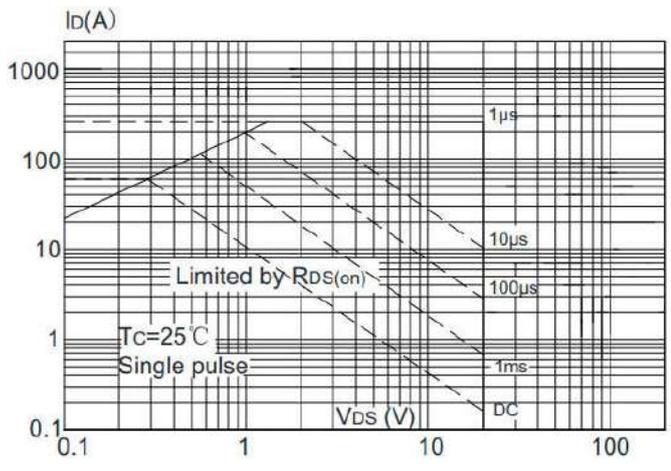


Figure 9: Maximum Safe Operating Area

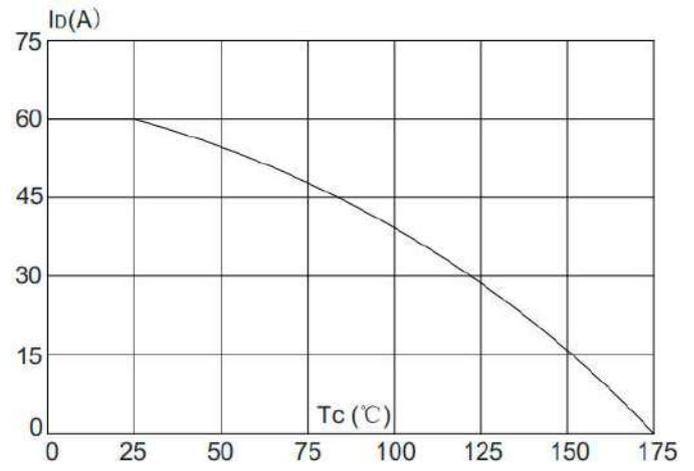
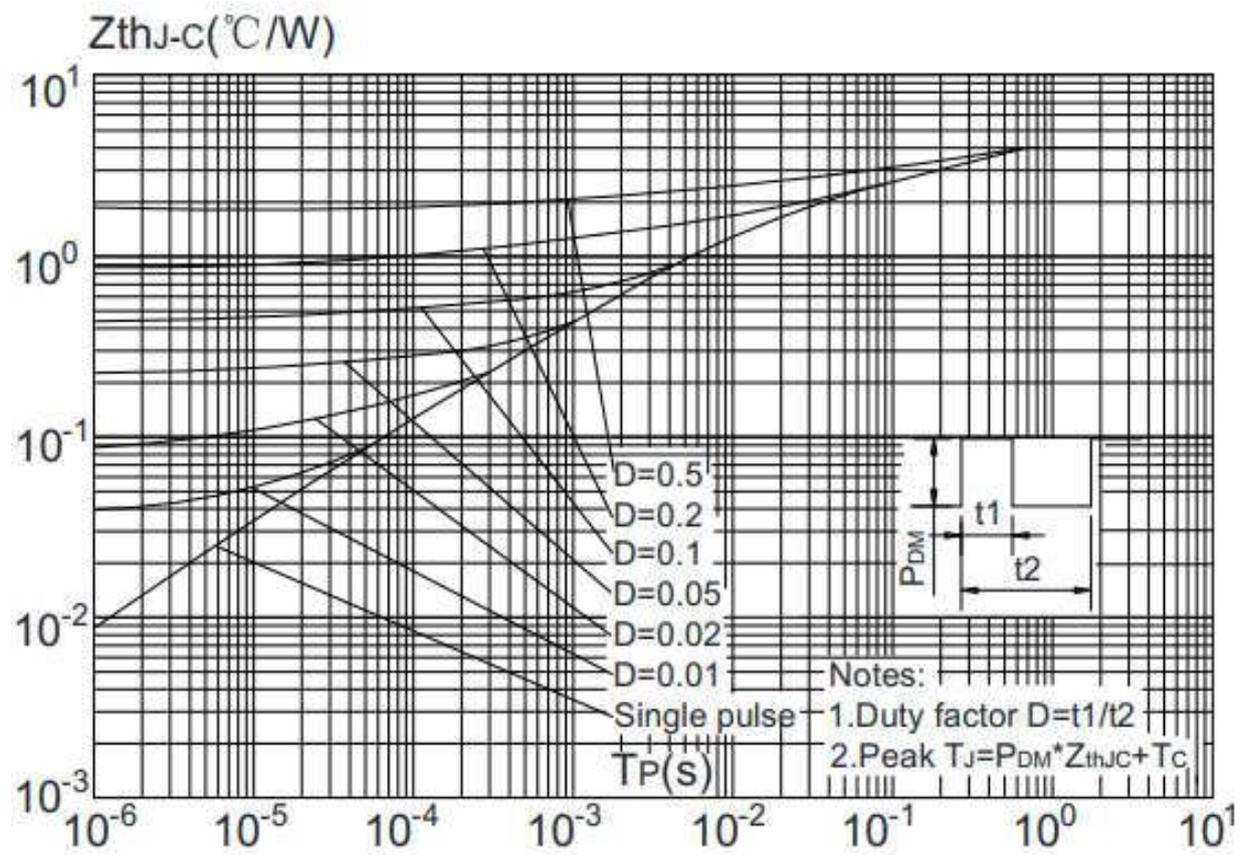


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuits and Waveforms

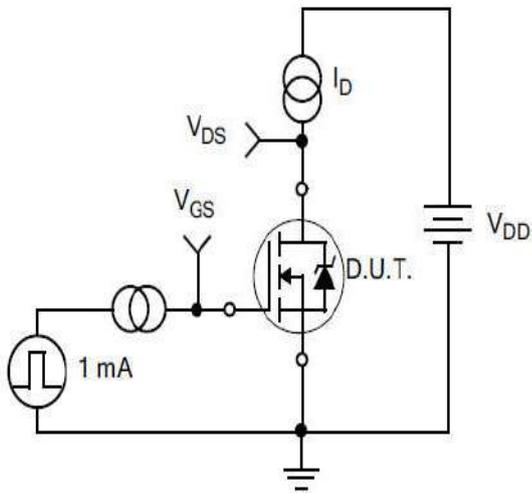


Figure A.
 Gate Charge Test Circuit

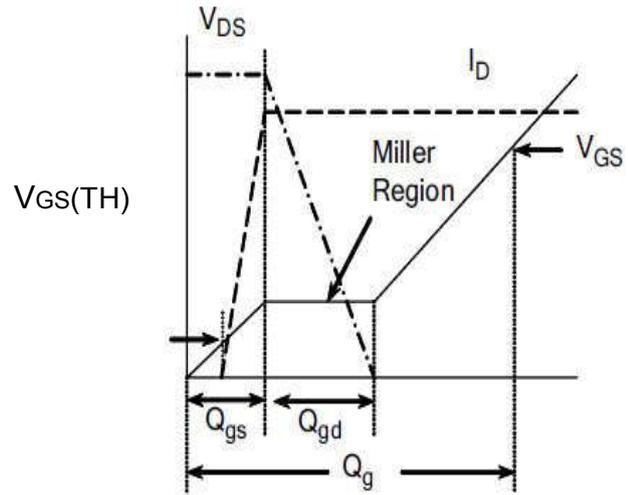


Figure B.
 Gate Charge Waveform

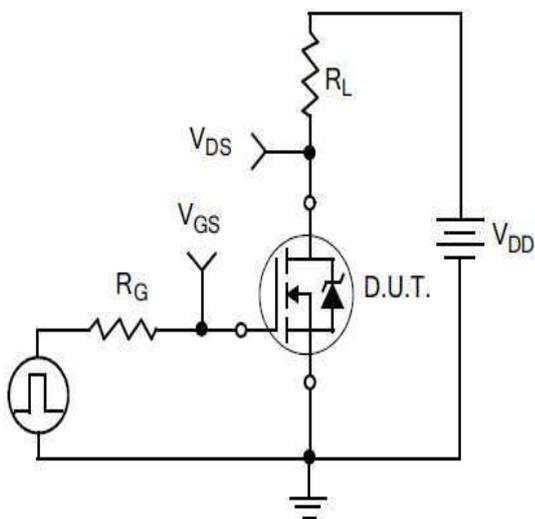


Figure C.
 Resistive Switching Test Circuit

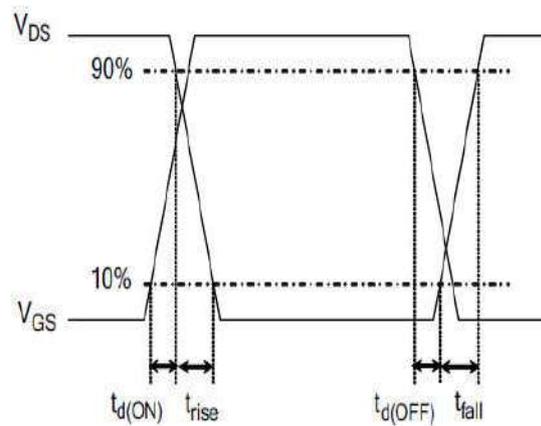


Figure D.
 Resistive Switching Waveforms

Test Circuits and Waveforms

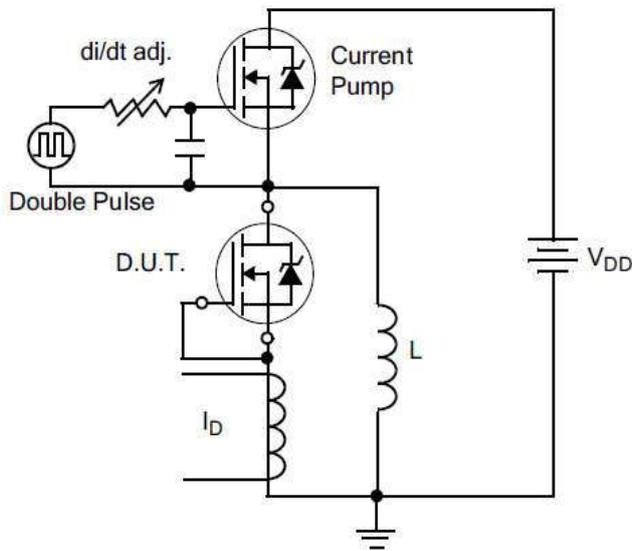


Figure E. Diode Reverse Recovery Test Circuit

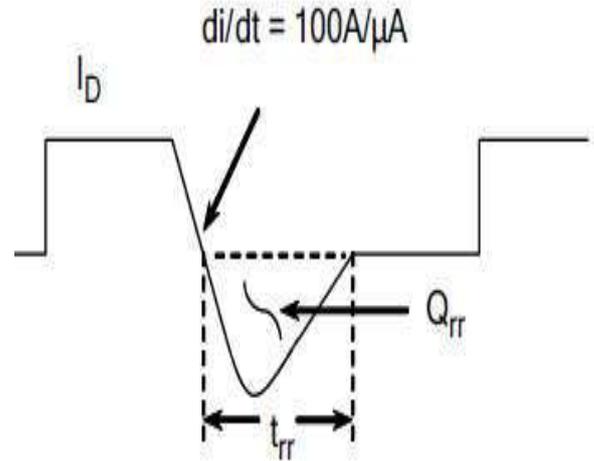


Figure F. Diode Reverse Recovery Waveform

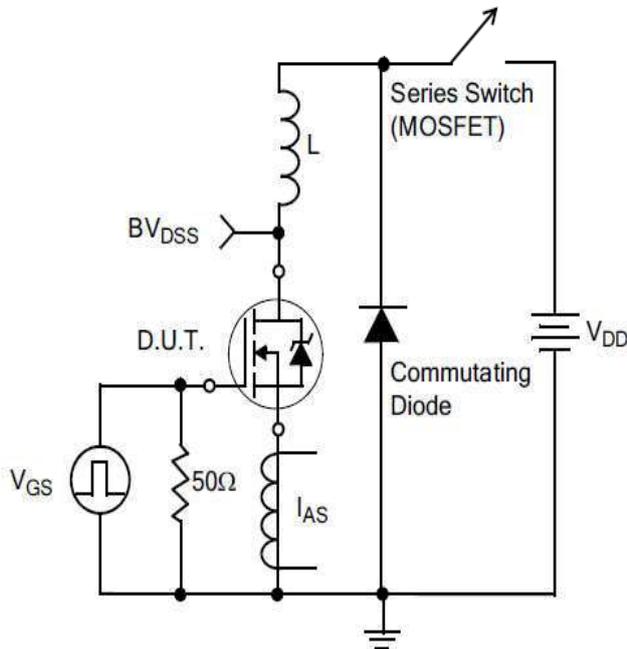
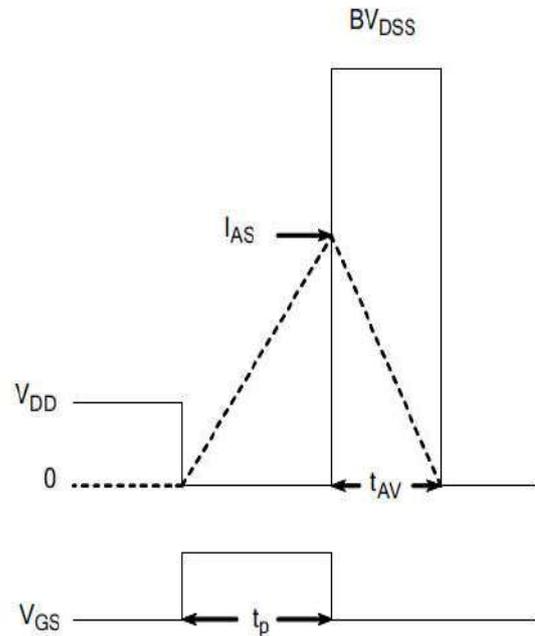


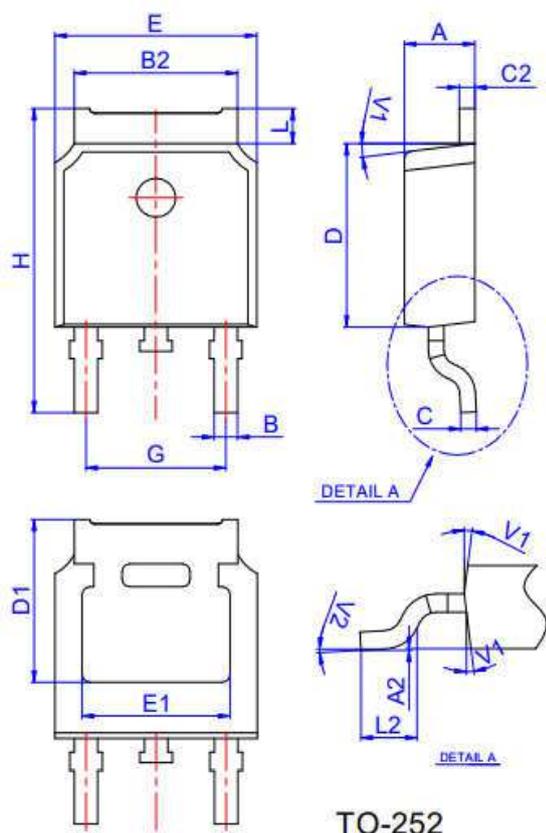
Figure G. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

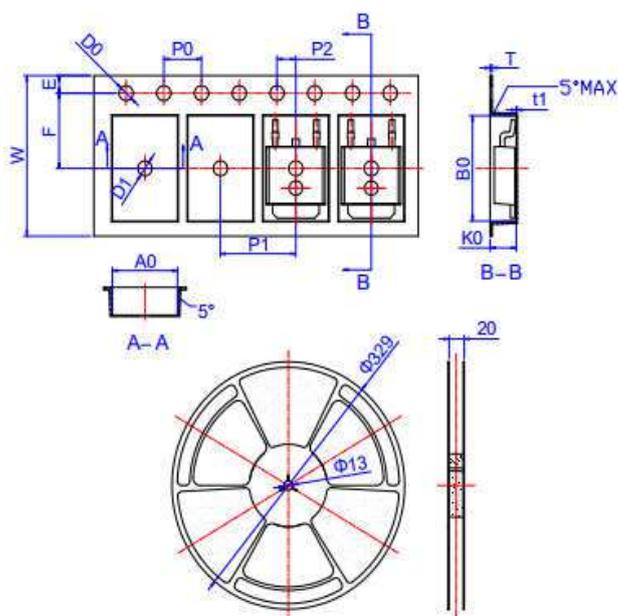
Figure H. Unclamped Inductive Switching Waveforms

Package outline drawing



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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 - b.support or sustain life,
 - c.whose failuer to when properly used in accordance with instructions for used provided in the laeling,can be reasonably expected to result in significant injury to the user.

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